



### **600V N-Channel Super Junction MOSFET**

Voltage

600 V

Current

20 A

#### **Features**

- $R_{DS(ON)}$ ,  $V_{GS}$ @10V,  $I_{D}$ @10A<0.196 $\Omega$
- Fast switching speed
- Low on-resistance
- Low Noise
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

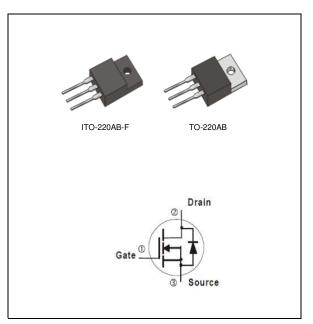
#### **Mechanical Data**

• Case: TO-220AB, ITO-220AB-F Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• TO-220AB Approx. Weight: 0.067 ounces, 1.89 grams

• ITO-220AB-F Approx. Weight: 0.068 ounces, 2 grams



### Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	TO-220AB	ITO-220AB-F	UNITS
Drain-Source Voltage		$V_{DS}$	600		_ v
Gate-Source Voltage		$V_{GS}$	<u>+</u> 20		V
Continuous Drain Current (Note 4)	T <sub>C</sub> =25°C		20		A
	T <sub>C</sub> =100°C	l <sub>D</sub>	13		
Pulsed Drain Current (Note 1)		I <sub>DM</sub>	60		
Power Dissipation	T <sub>C</sub> =25°C	P <sub>D</sub>	231	68	147
	T <sub>C</sub> =100°C		92	27	W
Continuous Drain Current (Note 4)	T <sub>A</sub> =25°C		2.1		A
	T <sub>A</sub> =70°C	l <sub>D</sub>	1.7		
Power Dissipation	T <sub>A</sub> =25°C	P <sub>D</sub>	2	1.04	147
	T <sub>A</sub> =70°C		1.3	0.9	W
Single Pulse Avalanche Energy (Note 5)		E <sub>AS</sub>	405		mJ
Operating Junction and		$T_J, T_{STG}$	EE 150		°C
Storage Temperature Range			-55~150		U
Typical Thermal Resistance (Note 4,5)		$R_{ heta JC}$	0.54	1.84	°C/W
		$R_{\theta JA}$	62.5	120	C/ <b>VV</b>

• Limited only By Maximum Junction Temperature





## **Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	600	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250uA$	2	2.95	4	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =10A	-	0.17	0.196	Ω
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ =600V, $V_{GS}$ =0V	-	-	1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	<u>+</u> 100	nA
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =20A, V <sub>GS</sub> =0V	-	0.97	1.5	V
Transconductance	GFS	VDS=10V, ID=10A	-	10	-	S
Dynamic (Note 6)						
Total Gate Charge	$Q_g$	V 000V I 15A	-	62	-	nC
Gate-Source Charge	$Q_gs$	$V_{DS}=300V, I_{D}=15A,$ $V_{GS}=10V$ (Note 2,3)	-	8	-	
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> =10V	-	34	-	
Gate Input Resistance	$R_g$	F = 1MHz	-	6.2	-	Ω
Input Capacitance	Ciss	)/ OF)/ )/ O)/	-	1421	-	pF
Output Capacitance	Coss	$V_{DS}=25V$ , $V_{GS}=0V$ ,	-	1427	-	
Reverse Transfer Capacitance	Crss	f=1MHZ	-	160	-	
Turn-On Delay Time	td <sub>(on)</sub>	V 000V 1 7.54	-	16	-	ns
Turn-On Rise Time	t <sub>r</sub>	$V_{DD}=300V, I_{D}=7.5A,$ $R_{G}=10\Omega$ (Note 2,3)	-	32	-	
Turn-Off Delay Time	td <sub>(off)</sub>	$R_{G}=10\Omega$	-	152	-	
Turn-Off Fall Time	t <sub>f</sub>		-	32	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I <sub>S</sub>		-	-	20	A
Maximum Pulsed Drain-Source Diode Forward Current	I <sub>SM</sub>		-	-	60	
Reverse Recovery Time	trr	V <sub>GS</sub> =0V, I <sub>S</sub> =20A	-	258	-	ns
Reverse Recovery Charge	Qrr	$dI_F/dt=100A/us^{(Note 2)}$	-	2.44	-	uC

#### NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150°C. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub> =25°C.
- 4. The maximum current rating is package limited.
- 5. L=70mH,  $I_{AS}$ =3.4A,  $V_{DD}$ =50V,  $R_{G}$ =25 ohm, Starting  $T_{J}$ =25°C.
- 6. Guaranteed by design, not subject to production testing.





#### **TYPICAL CHARACTERISTIC CURVES**

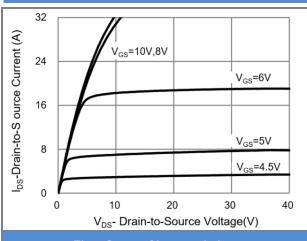


Fig.1 Output Characteristics

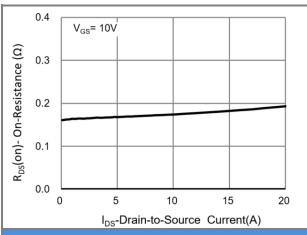


Fig.3 On-Resistance vs. Drain Current

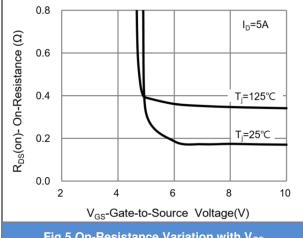
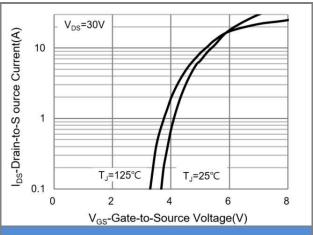


Fig.5 On-Resistance Variation with V<sub>GS</sub>



**Fig.2 Transfer Characteristics** 

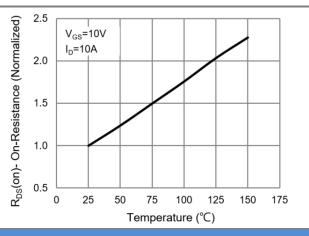


Fig.4 On-Resistance vs. Junction Temperature

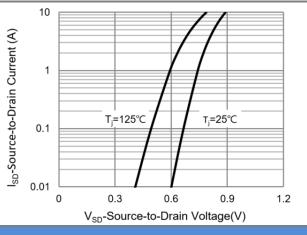


Fig.6 Source-Drain Diode Forward Voltage





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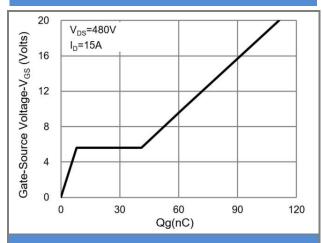


Fig.7 Gate-Charge Characteristics

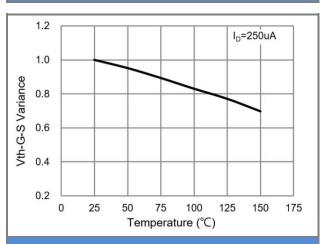


Fig.9 Threshold Voltage Variation with Temperature

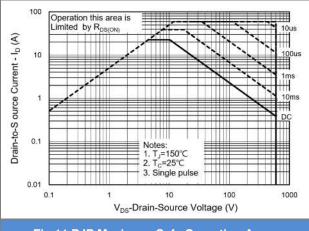


Fig.11 PJP Maximum Safe Operating Area

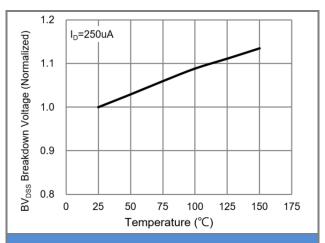


Fig.8 Breakdown Voltage Variation vs. Temperature

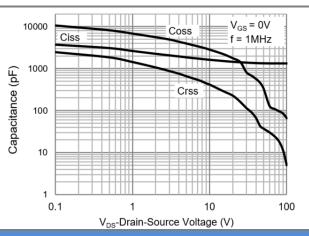


Fig.10 Capacitance vs. Drain-Source Voltage

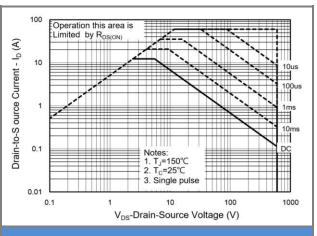


Fig.12 PJF Maximum Safe Operating Area





### **TYPICAL CHARACTERISTIC CURVES**

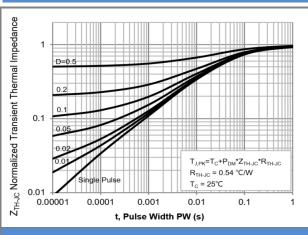
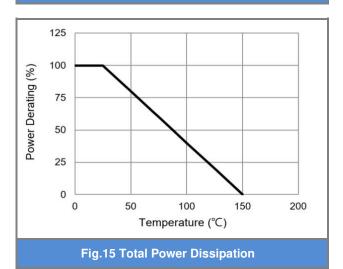


Fig.13 PJP Normalized Transient Thermal Impedance



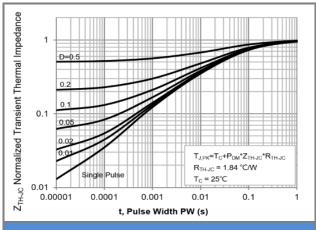
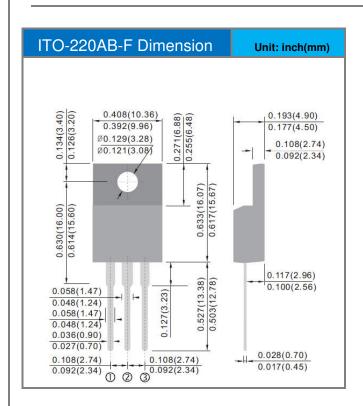


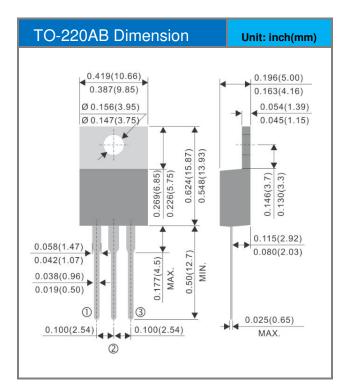
Fig.14 PJF Normalized Transient Thermal Impedance





### **Packaging Information**









### **Part No Packing Code Version**

Part No Packing Code	Package Type	Packing Type Marking		Version	
PJP60R190E_T0_00001	TO-220AB	50pcs / Tube	60R190E	Halogen free	
PJF60R190E_T0_00001	ITO-220AB-F	50pcs / Tube	60R190E	Halogen free	





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